

# 1MBI200U4H-120L-50

IGBT Modules

## IGBT MODULE (U series) 1200V / 200A / 1 in one package

### ■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

### ■ Applications

- Inverter DB for Motor Drive
- AC and DC Servo Drive Amplifier (DB)
- Active PFC
- Industrial machines



### ■ Maximum Ratings and Characteristics

#### ● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Collector-Emitter voltage	V <sub>CES</sub>		1200	V	
Gate-Emitter voltage	V <sub>GES</sub>		±20	V	
Collector current	I <sub>c</sub>	Continuous	Tc=25°C	300	A
			Tc=80°C	200	
	I <sub>c</sub> pulse	1ms	Tc=25°C	600	
			Tc=80°C	400	
	-I <sub>c</sub>			100	
-I <sub>c</sub> pulse	1ms		200		
Collector power dissipation	P <sub>c</sub>	1 device	1040	W	
Reverse voltage for FWD	V <sub>R</sub>		1200	V	
Forward current for FWD	I <sub>F</sub>	Continuous	300	A	
	I <sub>F</sub> pulse	1ms	600		
Junction temperature	T <sub>j</sub>		+150	°C	
Storage temperature	T <sub>stg</sub>		-40~+125	°C	
Isolation voltage	Between terminal and copper base (*1) V <sub>iso</sub>	AC : 1min.	2500	VAC	
Screw torque	Mounting (*2)	-	3.5	Nm	
	Terminals (*3)	-	4.5		

Note \*1: All terminals should be connected together when isolation test will be done.

Note \*2: Recommendable Value : 2.5 to 3.5 Nm (M5 or M6)

Note \*3: Recommendable Value : 2.5 to 3.5 Nm (M5)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	$I_{CES}$	$V_{GE} = 0V, V_{CE} = 1200V$	-	-	2.0	mA	
Gate-Emitter leakage current	$I_{GES}$	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	400	nA	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20V, I_c = 200mA$	4.5	6.5	8.5	V	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_c = 200A$	Tj=25°C	-	2.10	2.25	V
			Tj=125°C	-	2.30	-	
	$V_{CE(sat)}$ (chip)		Tj=25°C	-	1.90	2.05	
			Tj=125°C	-	2.10	-	
Input capacitance	$C_{ies}$	$V_{GE} = 0V, V_{CE} = 10V, f = 1MHz$	-	22	-	nF	
Turn-on time	$t_{on}$	$V_{CC} = 600V, I_c = 200A$ $V_{GE} = \pm 15V, R_G = 3\Omega$	-	0.32	1.20	$\mu s$	
	$t_r$		-	0.10	0.60		
	$t_r(i)$		-	0.03	-		
Turn-off time	$t_{off}$		-	0.41	1.00		
	$t_f$		-	0.07	0.30		
	$t_{tr}$		-	-	-		
Forward on voltage	$V_F$ (terminal)	$V_{GE} = 0V$ $I_F = 100A$	Tj=25°C	-	1.75	1.90	V
			Tj=125°C	-	1.85	-	
	$V_F$ (chip)		Tj=25°C	-	1.60	1.75	
			Tj=125°C	-	1.75	-	
Reverse Current	$I_R$	$V_{CE} = 1200V$	-	-	3.0	mA	
Forward on voltage	$V_F$ (terminal)	$V_{GE} = 0V$ $I_F = 300A$	Tj=25°C	-	1.85	2.00	V
			Tj=125°C	-	2.00	-	
	$V_F$ (chip)		Tj=25°C	-	1.60	1.75	
			Tj=125°C	-	1.75	-	
Reverse recovery time	$t_{rr}$	$I_F = 300A$	-	-	0.35	$\mu s$	
Lead resistance, terminal-chip(*4)	R lead		-	1.00	-	mΩ	

Note \*4: Biggest internal terminal resistance among arm.

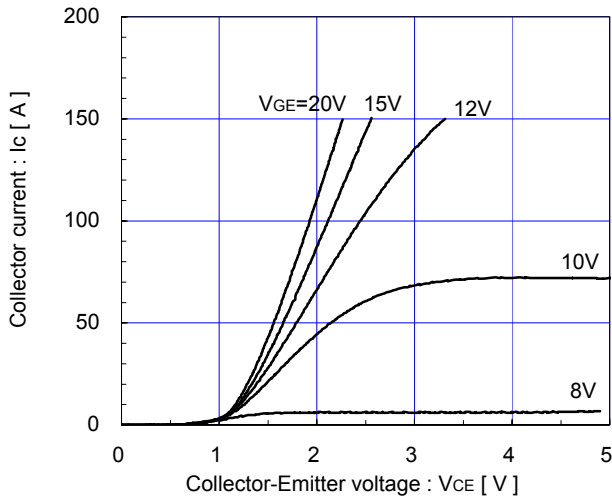
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	Rth(j-c)	IGBT	-	-	0.12	°C/W
		Inverse Diode	-	-	0.40	
		FWD	-	-	0.13	
Contact thermal resistance	Rth(c-f)	with Thermal Compound (*5)	-	0.025	-	

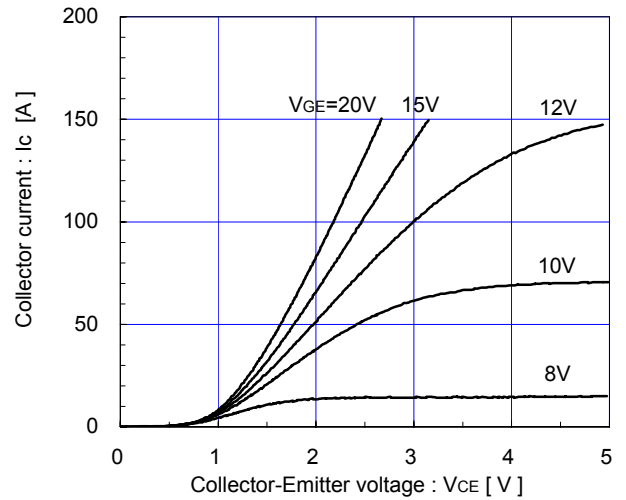
Note \*5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

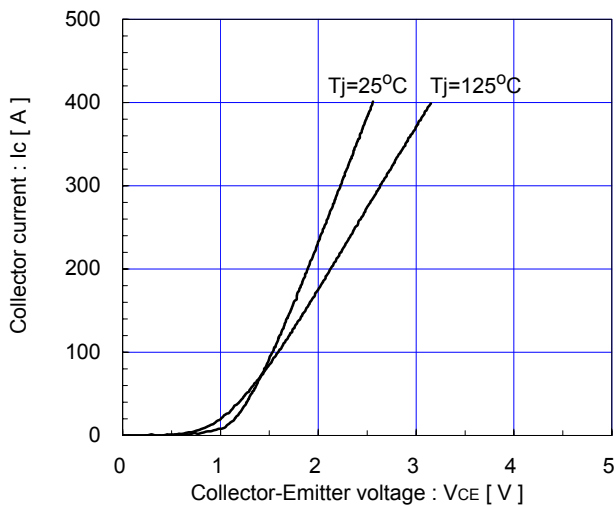
Collector current vs. Collector-Emitter voltage (typ.)  
Tj=25°C / chip



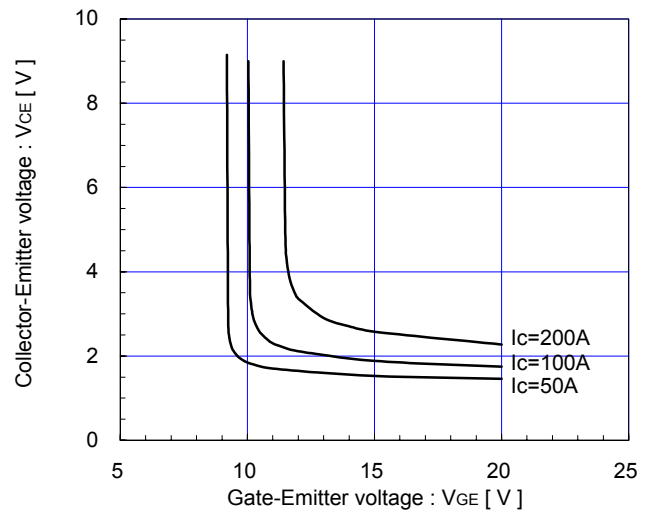
Collector current vs. Collector-Emitter voltage (typ.)  
Tj=125°C / chip



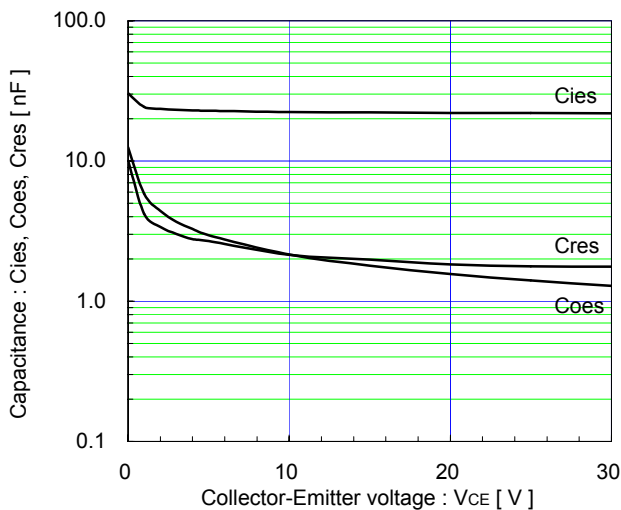
Collector current vs. Collector-Emitter voltage (typ.)  
VGE=15V / chip



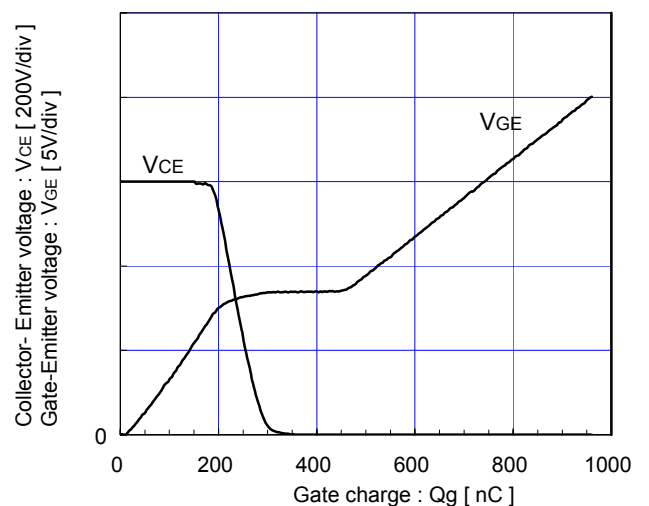
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)  
Tj=25°C / chip



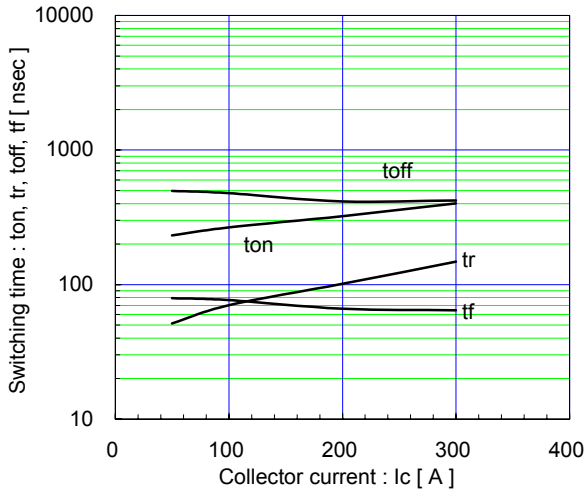
Capacitance vs. Collector-Emitter voltage (typ.)  
VGE=0V, f=1MHz, Tj=25°C



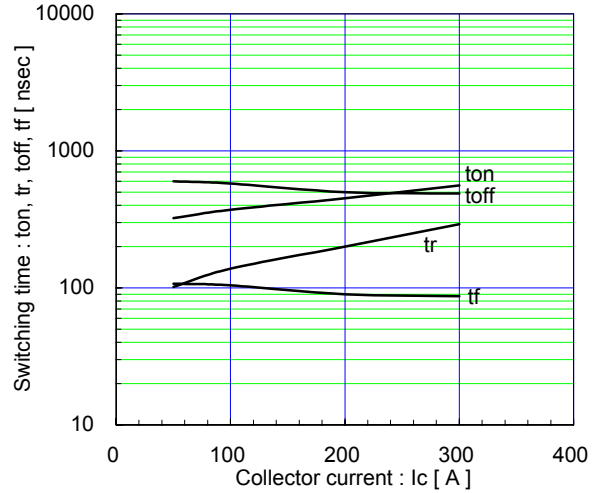
Dynamic Gate charge (typ.)  
Vcc=600V, Ic=200A, Tj=25°C



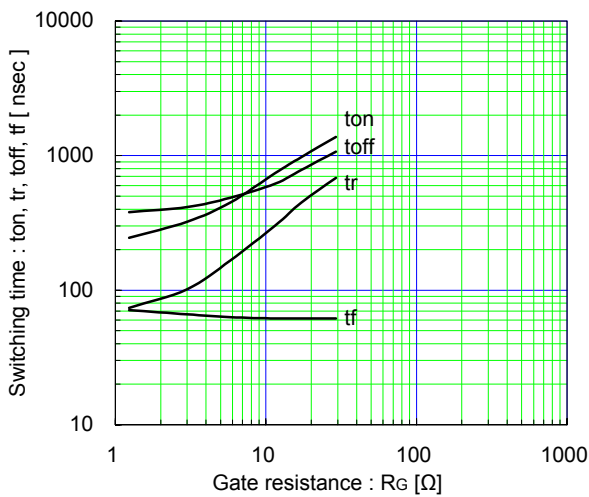
Switching time vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=3\Omega, T_j=25^\circ C$



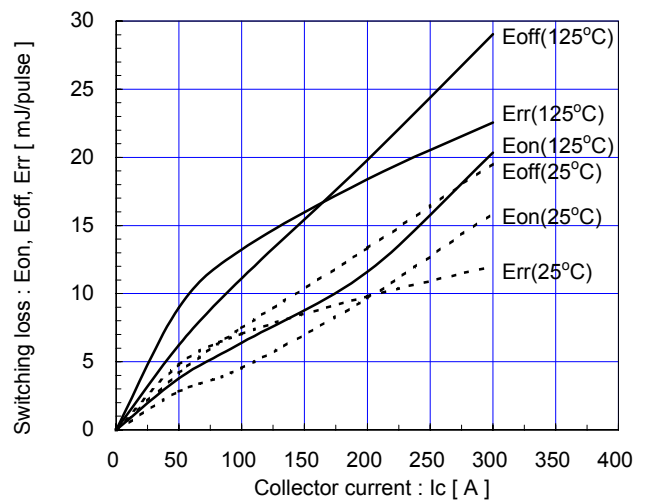
Switching time vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=3\Omega, T_j=125^\circ C$



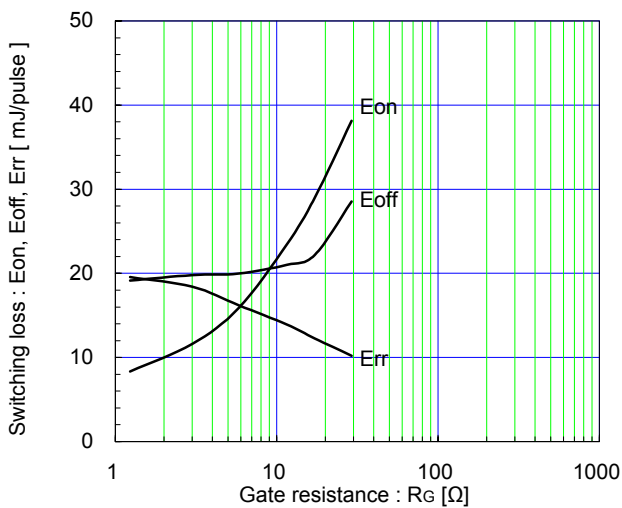
Switching time vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=200A, V_{GE}=\pm 15V, T_j=25^\circ C$



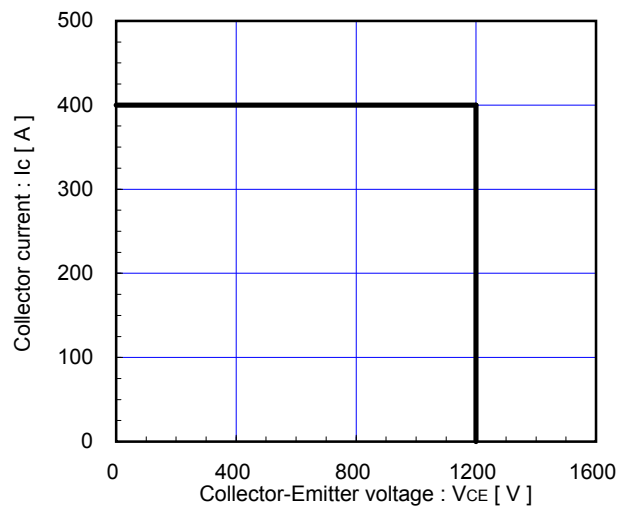
Switching loss vs. Collector current (typ.)  
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=3\Omega$

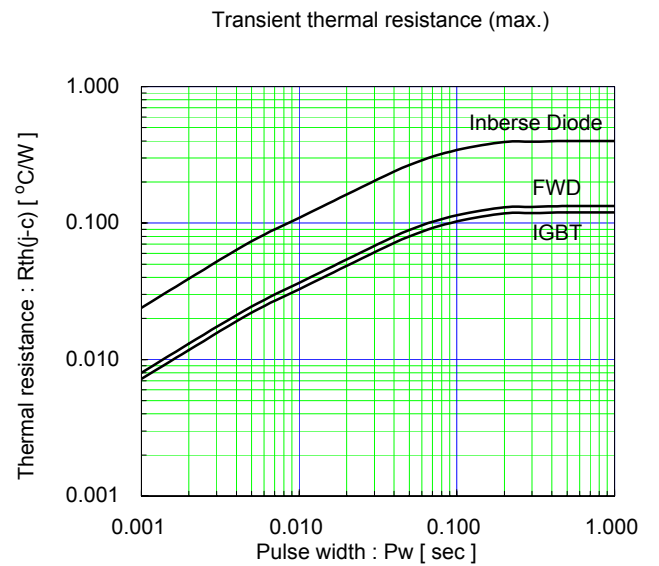
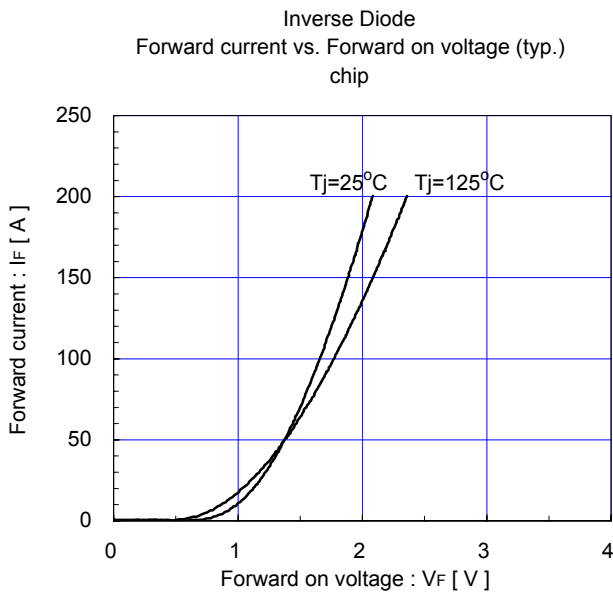
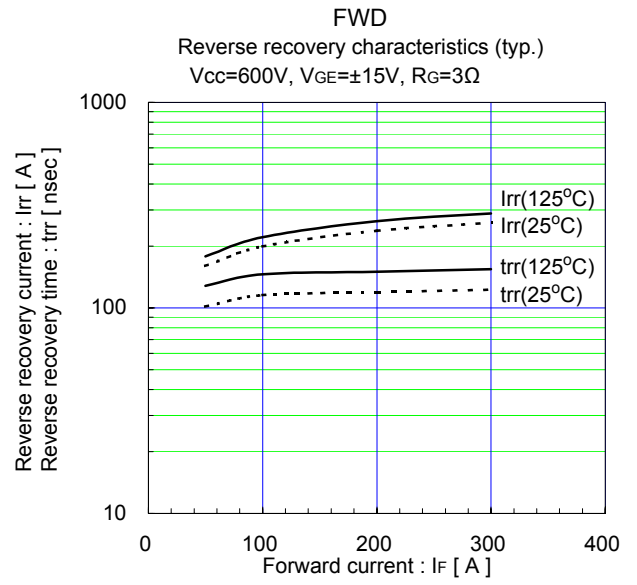
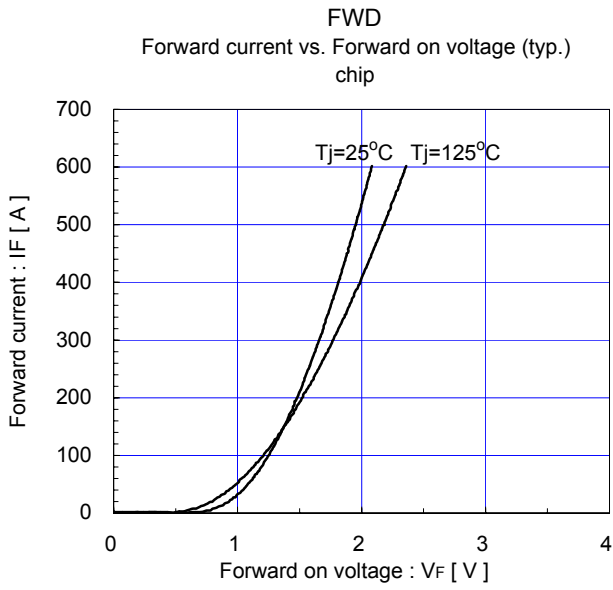


Switching loss vs. Gate resistance (typ.)  
 $V_{CC}=600V, I_c=200A, V_{GE}=\pm 15V, T_j=125^\circ C$

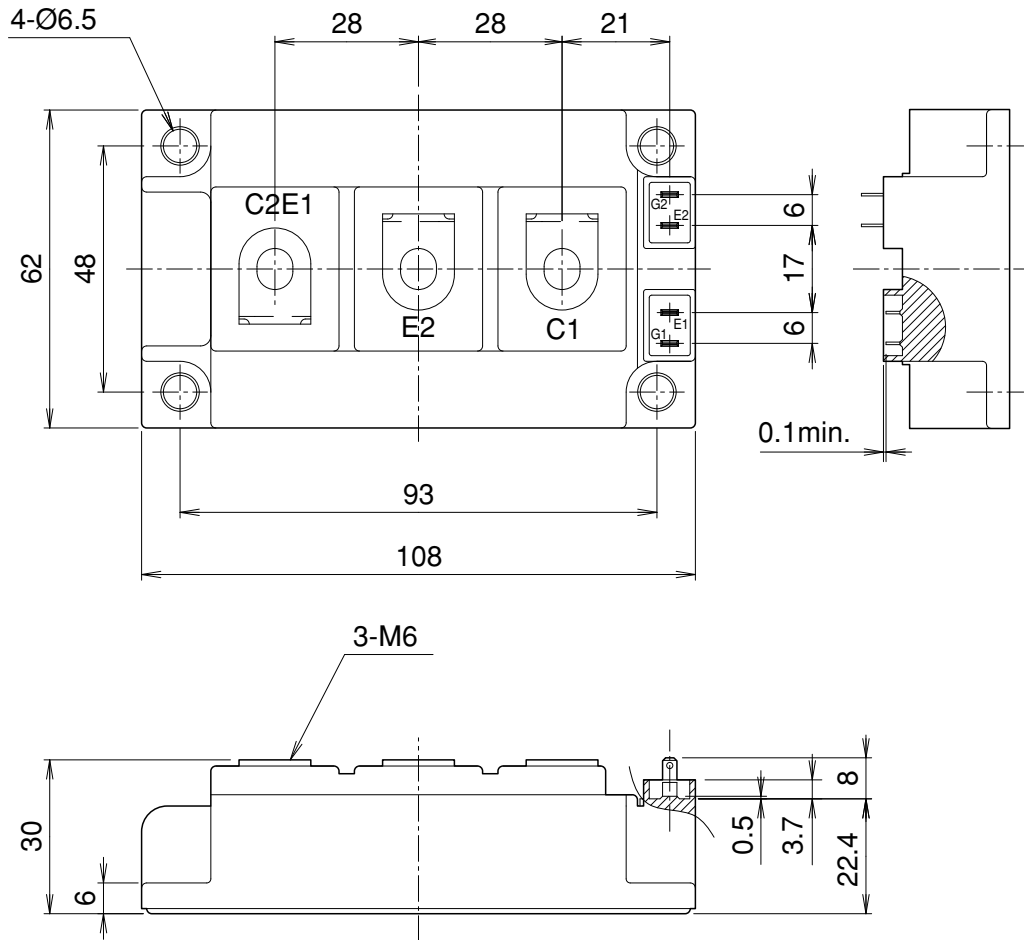


Reverse bias safe operating area (max.)  
 $+V_{GE}=15V, -V_{GE} \le 15V, R_G \ge 3\Omega, T_j \le 125^\circ C$

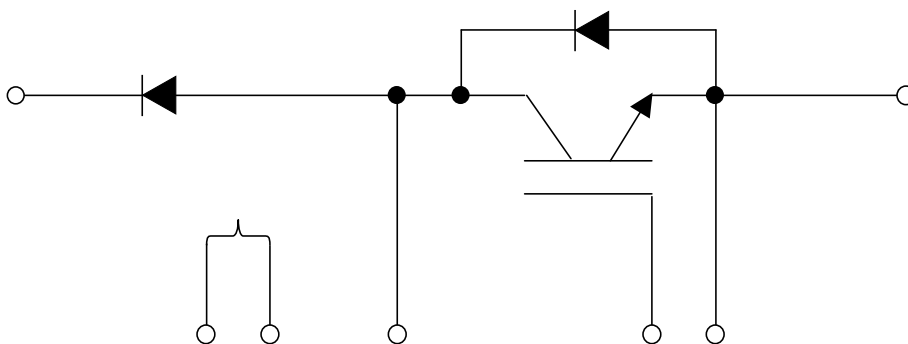




■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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